Features

- Interdigitated amplifying gates
- Fast turn-on and high di/dt
- Low switching losses

Typical Applications

- Inductive heating
- Electronic welders
- Self-commutated inverters

$I_{T(AV)}$	**4200A**
V_{DRM}/V_{RRM}	**1600 ～ 2200V**
t_q	**30~60μs**
I_{TSM}	**45 kA**
I^2t	**10125 10^3A^2S**

SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(°C)	VALUE			UNIT
					Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Double side cooled,	T_C=55°C	125			4200	A
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	tp=10ms		125	1600		2200	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}		125			250	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=0.6V_{RRM}		125			45	kA
I^2t	I^2t for fusing coordination						10125	A^2s*10^3
V_{TO}	Threshold voltage			125			1.14	V
r_T	On-state slope resistance						0.12	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=5000A, F=70kN		25			1.80	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=0.67V_{DRM}		125			1000	V/μs
di/dt	Critical rate of rise of on-state current	V_{DM}= 67%V_{DRM}, to4000A Gate pulse $t_r \leq 0.5\mu s$ I_{GM}=1.5A		125			1200	A/μs
Q_{rr}	Recovery charge	I_{TM}=2000A, tp=4000μs, di/dt=-20A/μs,V_R=100V		125		1100		μC
tq	Circuit commutated turn-off time	I_{TM}=2000A,tp=4000μs, V_R=100V dv/dt=30V/μs ,di/dt=-20A/μs		125	30		60	μs
I_{GT}	Gate trigger current	V_A=12V, I_A=1A		25	40		450	mA
V_{GT}	Gate trigger voltage				0.9		4.5	V
I_H	Holding current				20		1000	mA
V_{GD}	Non-trigger gate voltage	V_{DM}=67%V_{DRM}		125			0.3	V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C double side cooled Clamping force 70 kN					0.007	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.002	
F_m	Mounting force				50		70	kN
T_{stg}	Stored temperature				-40		140	°C
W_t	Weight					1390		g
Outline	P19							

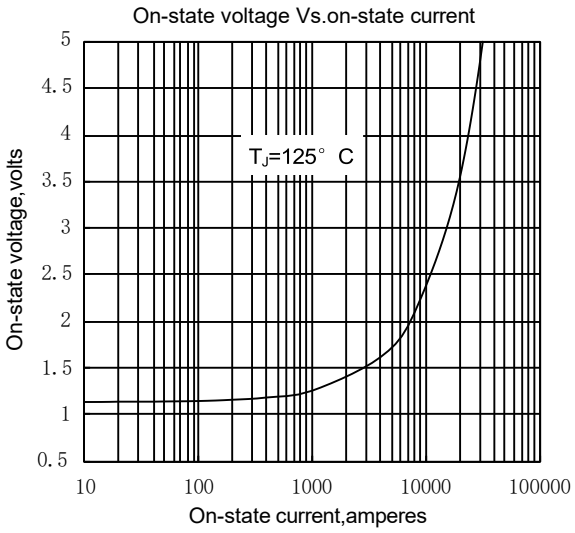


Fig.1

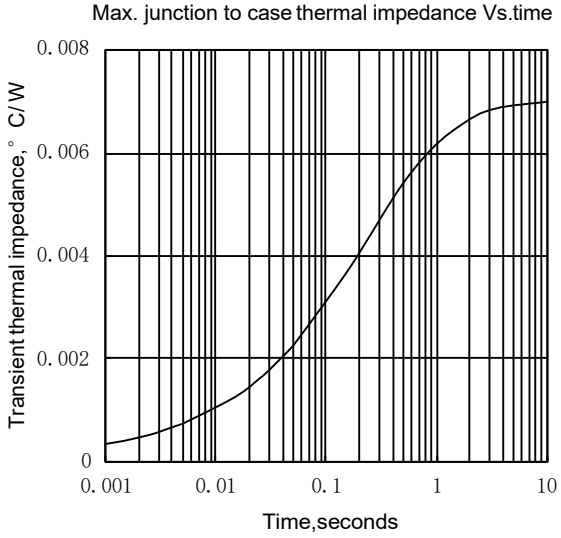


Fig.2

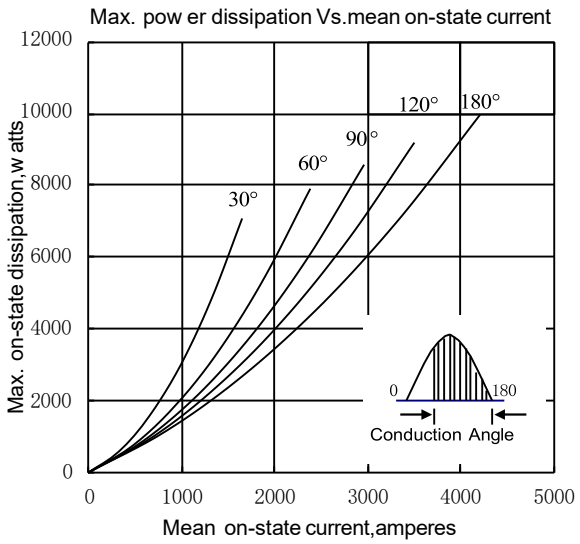


Fig.3

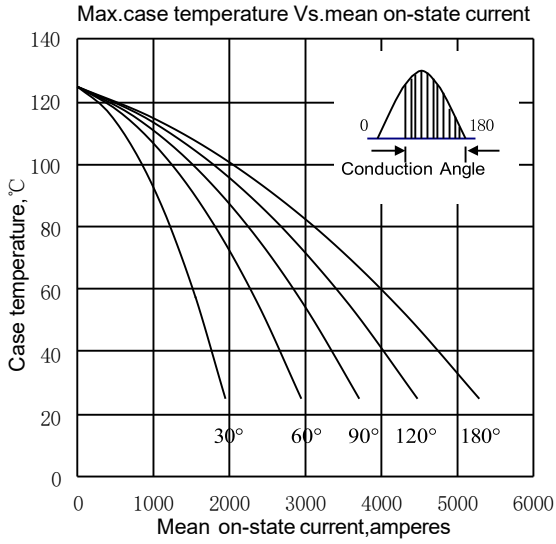


Fig.4

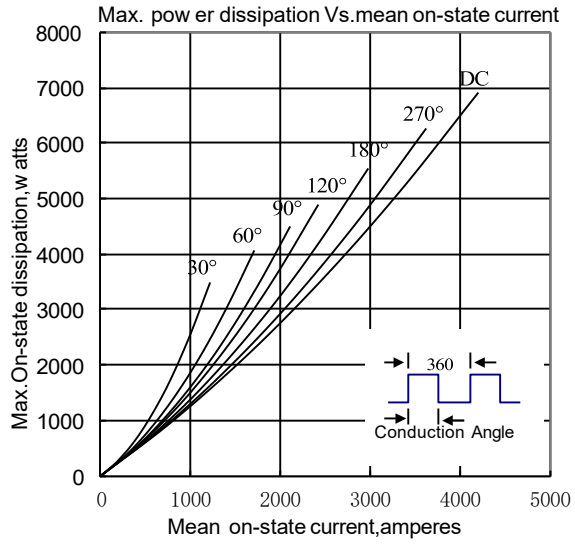


Fig.5

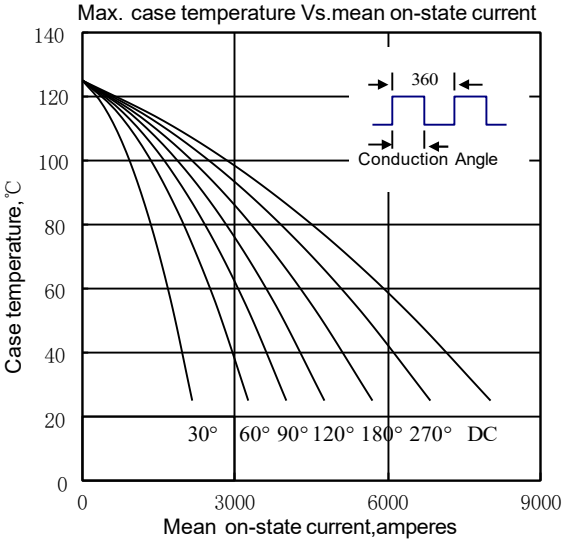


Fig.6

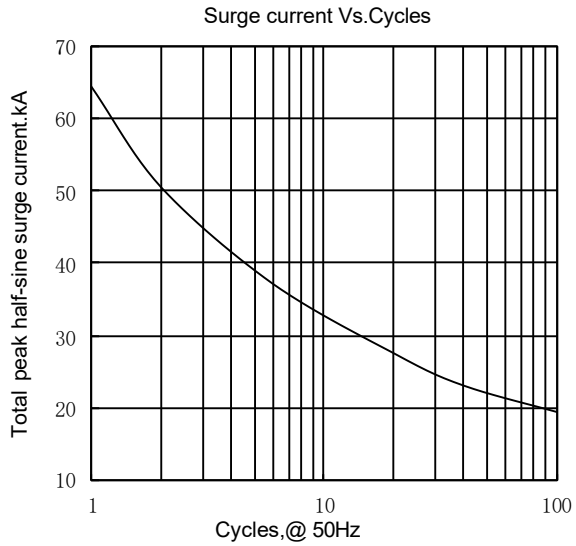


Fig.7

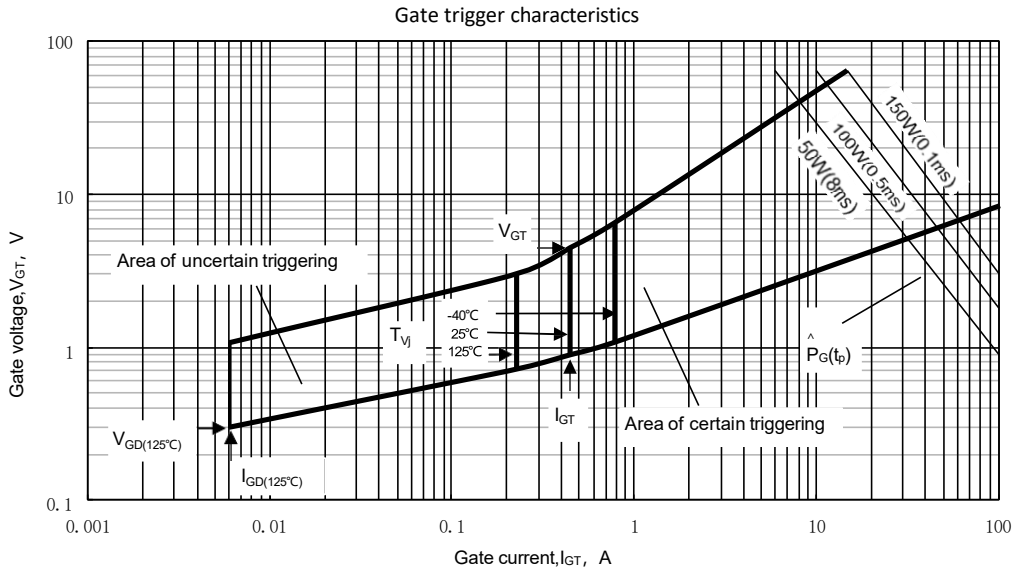
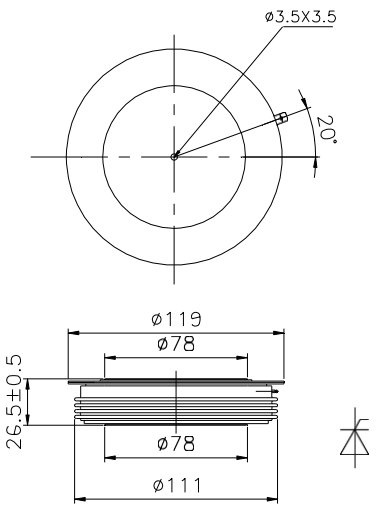


Fig.8

Outline:



NIps reserves the right to change specifications without notice.

2026-02